

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Voltage Drop
- Isolated MMC Base plate With AlN Substrates
- Dual Diodes Can Be Paralleled for 800A Rating

APPLICATIONS

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuits
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM400XXM65-K000 is a dual 6500 volt, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM400XXM65-K000

Note: When ordering, please use the complete part number.

KEY PARAMETERS

V_{RRM}		6500V
V_F	(typ)	3.6V
I_F	(max)	400A
I_{FM}	(max)	800A

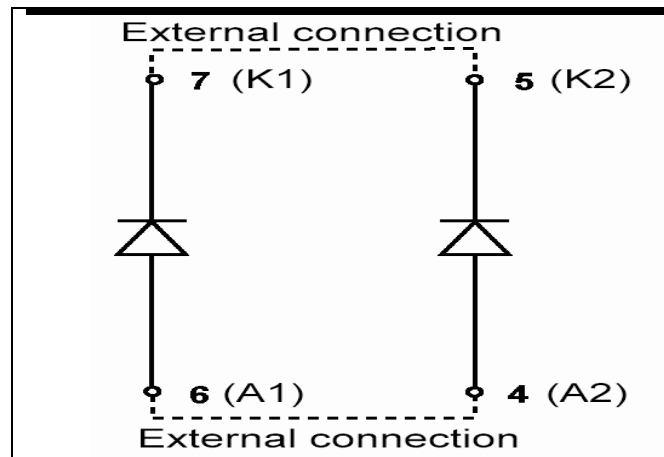


Fig. 1 Circuit diagram

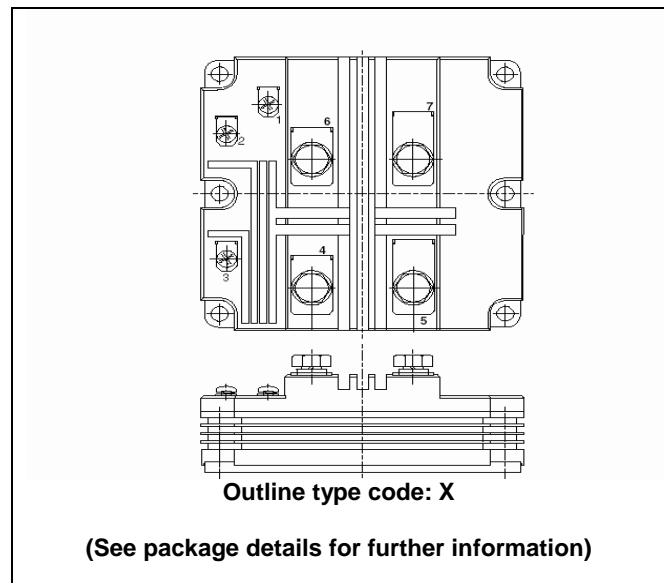


Fig. 2 Electrical connections (not to scale)

ABSOLUTE MAXIMUM RATINGS – PER ARM

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{RRM}	Repetitive peak reverse voltage	T _{vj} = 125°C T _{vj} = 25°C T _{vj} = -40°C	6500 6300 5800	V
I _F	Forward current (per arm)	DC, T _{case} = 75°C	400	A
I _{FM}	Max. forward current	T _{case} = 115°C, t _p = 1ms	800	A
I ² t	I ² t value fuse current rating	V _R = 0, t _p = 10ms, T _{vj} = 125°C	97	kA ² s
P _{max}	Maximum power dissipation	T _{case} = 25°C, T _{vj} = 125°C	3300	W
I _{isol}	Isolation voltage	Commoned terminals to base plate, AC RMS, 1 min, 50Hz	10.2	kV
Q _{pd}	Partial discharge	IEC1287. V ₁ = 7000V, V ₂ = 5100V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation: AIN
 Baseplate material: AISiC
 Creepage distance: 56mm
 Clearance: 26mm
 CTI (Critical Tracking Index): >600

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R _{th(j-c)}	Thermal resistance – diode (per arm)	Continuous dissipation – junction to case	-	-	30	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T _j	Junction temperature	-	-40	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting – M6	-	-	5	Nm
-		Electrical connections – M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS – PER ARM

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{RM}	Peak reverse current	$V_R = 6500\text{V}, T_{vj} = 125^{\circ}\text{C}$	-	-	40	mA
V_F	Forward voltage	$I_F = 400\text{A}$	-	3.6		V
		$I_F = 400\text{A}, T_{vj} = 125^{\circ}\text{C}$	-	4.1		V
L	Inductance (per arm)	-	-	40	-	nH

STATIC ELECTRICAL CHARACTERISTICS

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
L_M	Module inductance	-	-	20	-	nH
R_{INT}	Internal resistance (per arm)			0.37		m Ω

DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{rr}	Peak reverse recovery current	$I_F = 400\text{V},$ $di_F/dt = 1300\text{A}/\mu\text{s},$ $V_R = 3600\text{V}$	-	300	-	A
Q_{rr}	Reverse recovery charge		-	700	-	μC
E_{rec}	Reverse recovery energy		-	1300	-	mJ

$T_{vj} = 125^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{rr}	Peak reverse recovery current	$I_F = 400\text{A},$ $di_F/dt = 1600\text{A}/\mu\text{s}$ $V_R = 3600\text{V}$	-	370	-	A
Q_{rr}	Reverse recovery charge		-	1000	-	μC
E_{rec}	Reverse recovery energy		-	2000	-	mJ

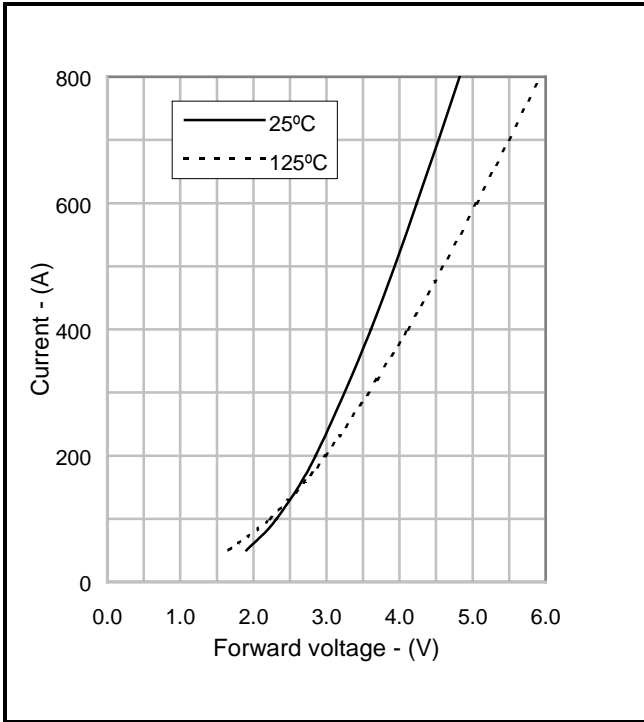


Fig.3 Diode typical forward characteristics

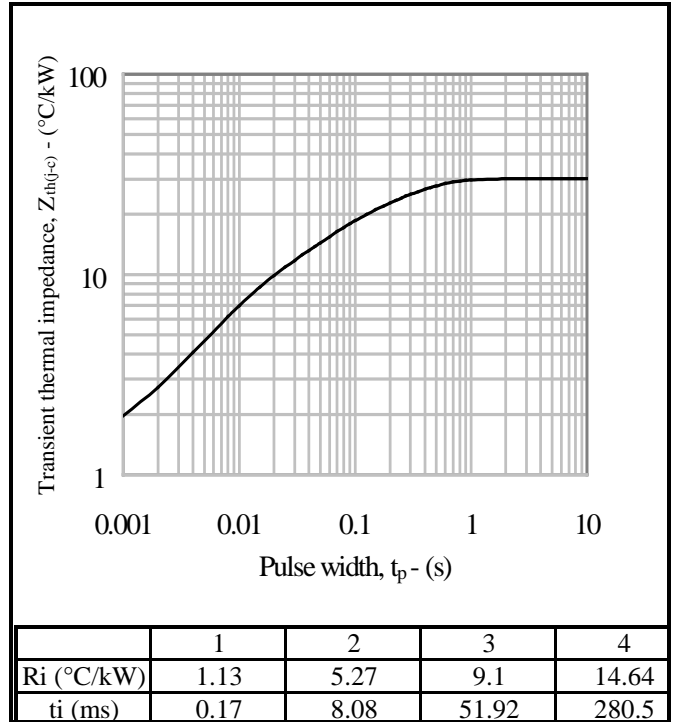


Fig.4 Transient thermal impedance

	1	2	3	4
Ri (°C/kW)	1.13	5.27	9.1	14.64
ti (ms)	0.17	8.08	51.92	280.5

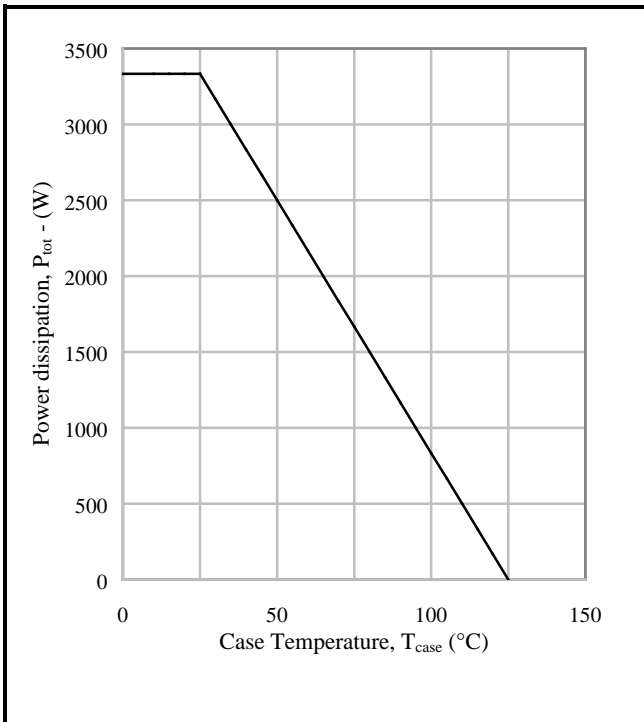


Fig.5 Power dissipation

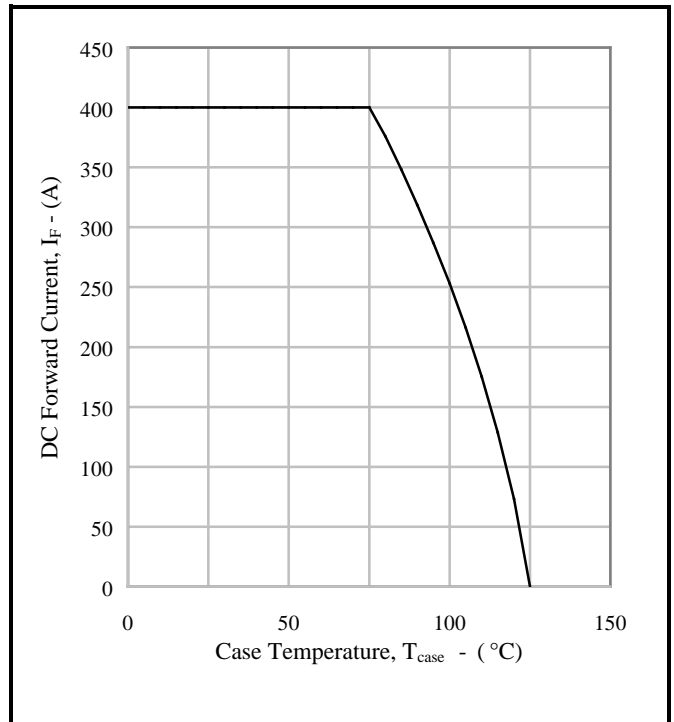


Fig.6 6DC current rating vs case temperature

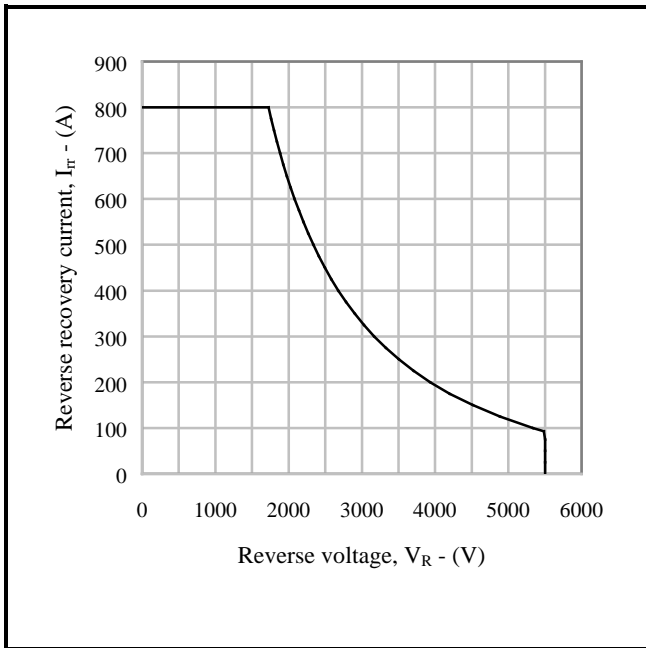
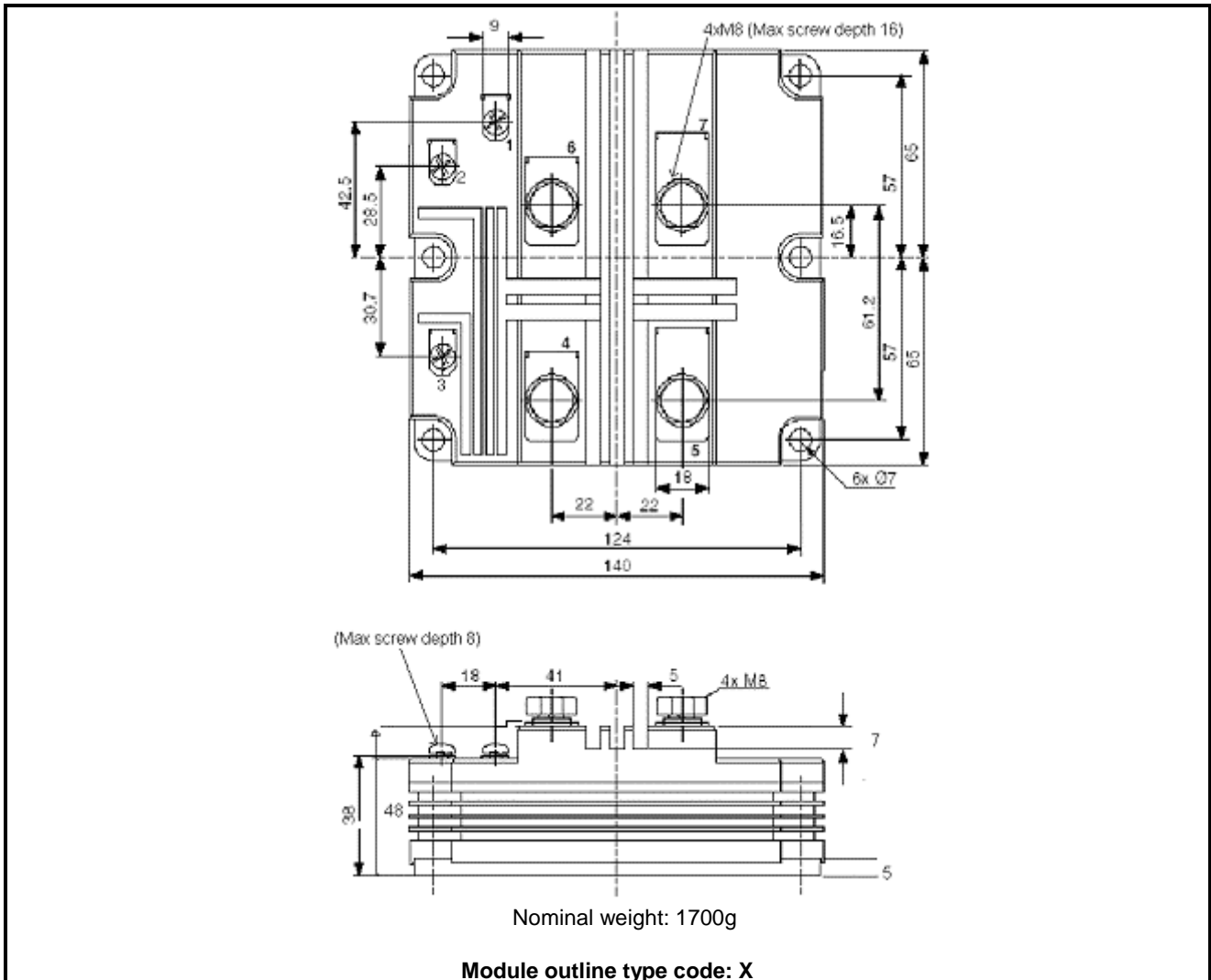


Fig.7 RBSOA

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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